SILICON PNP TRANSISTOR
EPITAXIAL PLANAR TYPE (PCT PROCESS)

KTA 562TM

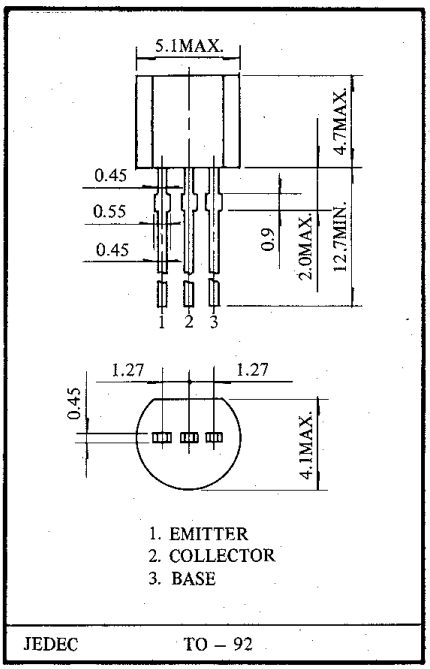
APPLICATIONS

- Low Frequency, Low Power Amplifiers
- General-driver Stage Amplifiers
- General Purpose Switching Applications

FEATURES

- Excellent h_{FE} vs. Collector Current Characteristics, $h_{FE}(2)$ = 25min. at V_{CE} = −6V, Ic = −400mA
- Ic max. = −500mA
- Pc max. = 500mW
- Complementary to the KTC 1959

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC TO − 92

MAXIMUM RATINGS (Ta = 25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector − Base Voltage	V_{CBO}	−35	V
Collector − Emitter Voltage	V_{CEO}	−30	V
Emitter − Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−500	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta = 25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut off Current	I_{CBO}	V_{CB} = −35V, I_E = 0	−	−	−0.1	μA
Emitter Cut off Current	I_{EBO}	V_{EB} = −5V, I_C = 0	−	−	−0.1	μA
DC Current Gain (1)	$h_{FE(1)}$	V_{CE} = −1V, I_C = −100mA	70	−	400	
DC Current Gain (2)	$h_{FE(2)}$ (Pulsed)	V_{CE} = −6V, I_C = −400mA	25	−	−	
Collector − Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = −100mA, I_B = −10mA	−	−0.1	−0.25	V
Base − Emitter Voltage	V_{BE}	I_C = −100mA, V_{CE} = −1V	−	−0.8	−1.0	V
Transition Frequency	f_T	V_{CE} = −6V, I_E = 20mA	−	200	−	MHz
Output Capacitance	C_{ob}	V_{CB} = −6V, I_E = 0, f = 1MHz	−	13	−	pF

Note : According to h_{FE} (1) Classified as follows

O	70~140	Y	120~240	GR	200~400